

Blue phosphorene-Based Heterostructures: Type-II Semiconductors with Direct Band Gap and Enhanced Visible Light Absorption for Optoelectronic Applications

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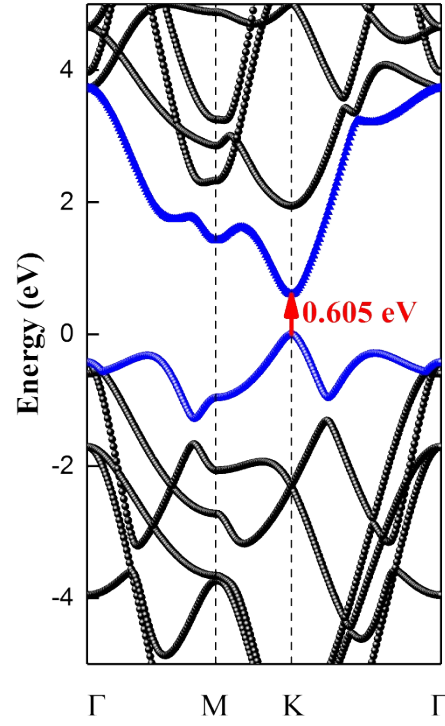


Fig. S1 The band structure of the ABIII pattern.

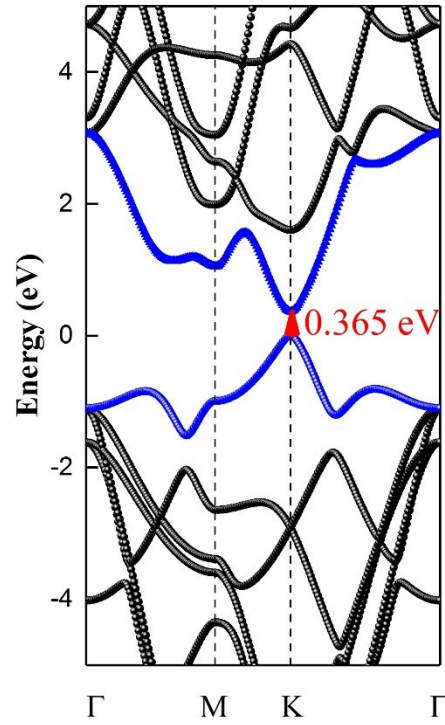


Fig. S2 The band structure of the ABIII pattern under an E -field of 0.001 a.u.

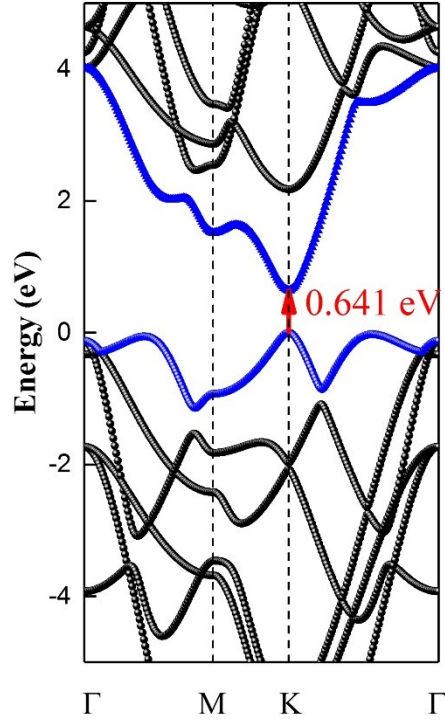


Fig. S3 The band structure of the ABIII pattern under an E -field of 0.002 a.u.

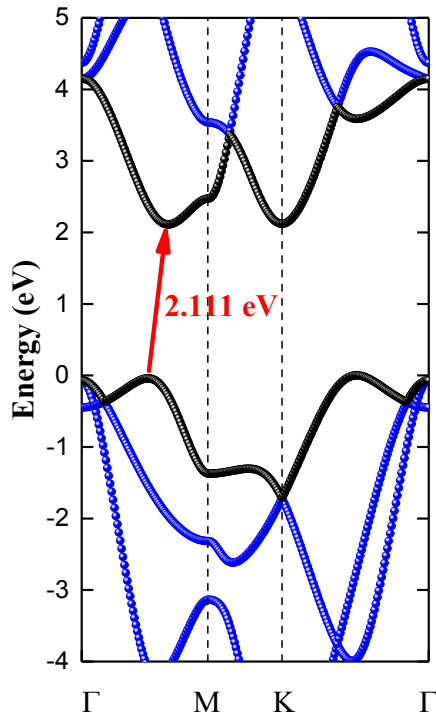


Fig. S4 The band structure of the isolated Blue-p with the same lattice constant